JL7012F Datasheet

Zhuhai Jieli Technology Co.,LTD

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JL7012F Features

CPU

- 32bit Dual-Core DSP
- Maximum speed 160MHz
- 32KB ICache and 16KB DCache
- IEEE754 Single precision FPU
- Mathematical accelerate engine
- Interrupts with 8 priority level

Memory

- On-chip 640KB SRAM
- Support MMU
- Built-In Flash

Clocks

- On-chip 16 MHz clock oscillator
- On-chip 200 kHz lower-temperature-drift clock oscillator
- 24 MHz crystal oscillator
- 32.768 kHz crystal oscillator

DSP Audio Processing

- SBC/mSBC encoder and decoder
- Support MP2, MP3, WMA, APE, FLAC, AAC, MP4, M4A, WAV, AIF, AIFC audio decoding
- Packet Loss Concealment (PLC) for voice processing
- Single/Dual MIC Environmental Noise Cancellation (ENC)
- Multi-band DRC limiter
- Multi-band EQ configuration for voice Effects

Audio Codec

- Two channels 24-bit DAC,SNR ≥ 98dB
- Four channels 24-bit ADC, SNR \geq 95dB
- Audio DAC Sampling rates of 8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32kHz/44.1kHz/48kHz/64kHz/88.2kHz/96kHz are supported
- Audio ADC Sampling rates of

8kHz/11.025kHz/16kHz/22.05kHz/24kHz/32 kHz/44.1kHz/48kHz are supported

- Support four digital/analog MIC inputs
- Four channels analog audio inputs
- Audio DAC support differential cap-less mode or single-ended mode
- Direct drive 16ohm/32ohm Speaker loading

Bluetooth

- Compliant with Bluetooth
 V5.3+BR+EDR+BLE specification
- Support AoA/AoD direction finding
- Support LE audio BIS/CIS full function
- Meet class2 and class3 transmitting power requirement
- Maximum +9dbm transmitting power
- EDR receiver with minimum -95dBm sensitivity
- Support a2dp\avctp\avdtp\avrcp\hfp\spp\smp\
 att\gap\gatt\rfcomm\sdp\l2cap profile
- bap 1.0\pacs 1.0\ccp 1.0\mcp 1.0\micp1.0\vcp 1.0\csip 1.0
- a2dp 1.3.2\avctp 1.4\avdtp 1.3\ avrcp 1.6.2\hfp 1.8 \spp 1.2\rfcomm 1.1\pnp 1.3\hid 1.1.1\sdp core5.3\l2cap core 5.3

Graphics

- 2D Graphics accelerator
- Support crop, scale, rotation process
- Support multiple data format graphics
- SPI and QSPI display driver

Peripherals

- One full speed USB OTG controller
- One SD host controller for eMMC/SD
- Six multi-function 32-bit timers, support capture and PWM mode
- Four UART interface,
 UART0,UART1&UART2 support DMA
- Two I2C Master/Slave interface
- Four SPI Master/Slave interface



- I2S Master/Slave interface
- QDEC
- Low power CapSense
- 15-channel 10-bit ADC for analog sampling
- 4-channel Motor PWM controller
- 40 Individually programmable and multiplexed GPIO pins
- Up to 12 external interrupt/wake-up source(low power available,can be multiplexed to any I/O)

PMU

- Built-in lithium battery charging manager,up to 200mA charging current
- Built-in LDO and Buck DC-DC converter
- Less than 2uA sleep current
- VPWR range : 4.5V to 5.5V

- **VBAT** range : 2.2V to 4.5V
- IOVDD range: 2.2V to 3.6V

Packages

QFN52(6mm*6mm)

Temperature

- Operating temperature: -40°C to +85°C
- Storage temperature: -65°C to +150°C

Applications

- Bluetooth Smart Watch
- Bluetooth Smart Home
- Bluetooth Intelligent Voice
- Bluetooth Stereo speaker
- Bluetooth TWS speaker
- Bluetooth alarm clock speaker



1 Block Diagram

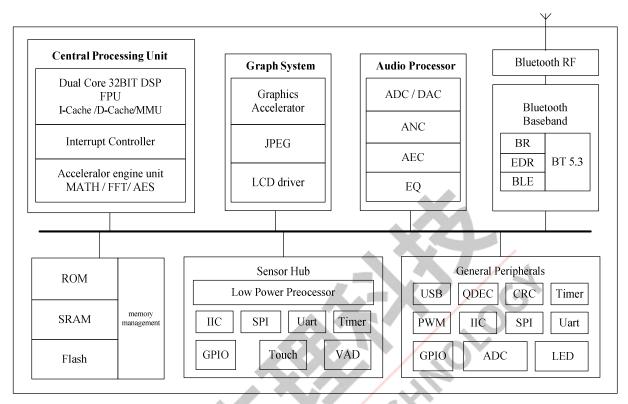


Figure 1-1 JL7012F Block Diagram



2 Pin Definition

2.1 Pin Assignment

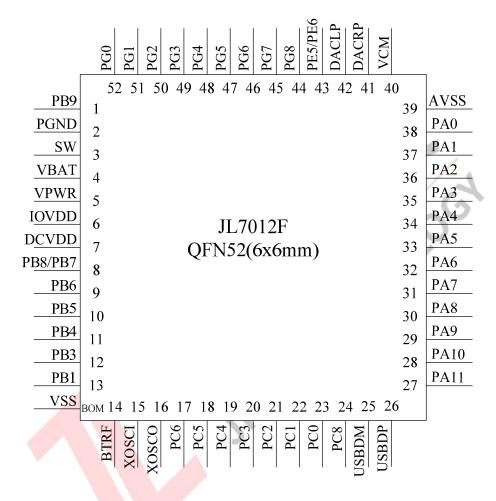


Figure 2-1 JL7012F Package Diagram



2.2 Pin Description

Table 2-1 JL7012F Pin Description

Table 2-1 9E/012F Till Description						
PIN NO.	Name	Type	Function	Other Function		
1	PB9	I/O	GPIO (High Voltage Resistant)	ADC9:ADC Input Channel 9;		
2	PGND	G		The ground of Buck DC-DC converter;		
3	SW	PO		Switch signal of the Buck converter, Connected to inductor;		
4	VBAT	P		Battery interface;		
5	VPWR (PP0)	PI (I/O)	GPIO (High Voltage Resistant)	Charging power input; UART0TXB:Uart0 Data Output(B); UART0RXB:Uart0 Data Input(B); CAP1:Timer1 Capture; PWM3:Timer3 PWM Output;		
6	IOVDD	PO		Built-in linear voltage regulator output;		
7	DCVDD	P	A	Internal power;		
8	PB8	I/O	GPIO (High Voltage Resistant)	CAP4:Timer4 Capture;		
8	PB7	I/O	GPIO (High Voltage Resistant)	OSC32KI:32.768khz crystal oscillator input;		
9	PB6	I/O	GPIO (High Voltage Resistant)	OSC32KO:32.768khz crystal oscillator output; PWM2:Timer2 PWM Output;		
10	PB5	I/O	GPIO (High Voltage Resistant)	LP_Touch4:Low Power Touch Channel 4; IIC1_SDA_A:IIC1 SDA(A); ADC8:ADC Input Channel 8; UART3RXB:Uart3 Data Input(B);		
11	PB4	I/O	GPIO (High Voltage Resistant)	LP_Touch3:Low Power Touch Channel 3; CLKOUT0:Clock Out0; IIC1_SCL_A:IIC1 SCL(A); UART3TXB:Uart3 Data Output(B); TMR2:Timer2 Clock Input;		
12	PB3	I/O	GPIO (High Voltage Resistant)	UART3RXA:Uart3 Data Input(A);		
13	PB1	I/O	GPIO (pull up) (High Voltage Resistant)	Hold down 0 to reset; LP_Touch1:Low Power Touch Channel 1; ADC6:ADC Input Channel 6;		
14	BTRF	RFI		Bluetooth RF antenna interface;		
15	XOSCI	I		System Crystal Oscillator Input;		
16	XOSCO	0		System Crystal Oscillator Output;		
17	PC6	I/O	GPIO (High Voltage Resistant)	ALNK_MCLKB:ALNK Master Clock(B);		



				GEGL DA GEGLD (A . 1)
				SFC1_D2:SFC1 Data2(nor flash);
				SPI0_DAT2C(2):SPI0 Data2(C);
	18 PC5 I/O GPIO			SD0_CLKA:SD0 Clock(A);
18			GPIO	SPI1DOB:SPI1 Data Out(B);
				IIC0_SDA_B:IIC0 SDA(B);
				ALNK_DAT3(B):Audio Link Data3(B);
				ADC5:ADC Input Channel 5;
				UART2RXA:Uart2 Data Input(A);
				SFC1_DI(D1):SFC1 Data In(nor flash);
				SPI0_DIC(1):SPI0 Data In(C);
				SD0_CMDA:SD0 CMD(A);
				SPI1CLKB:SPI1 Clock(B);
19	PC4	I/O	GPIO	IIC0_SCL_B:IIC0 SCL(B);
				ALNK_DAT2(B):Audio Link Data2(B);
				ADC4:ADC Input Channel 4;
				UART2TXA:Uart2 Data Output(A);
				PWM4:Timer4 PWM Output;
				SFC1_CS:SFC1 Chip Select(nor flash);
				LNA_EN:LNA Enable;
				SPI0_CSC:SPI0 Chip Select(C);
20	PC3	I/O	GPIO	SD0_DATA:SD0 Data(A);
			26-1	SPI1DIB:SPI1 Data In(B);
			1	ALNK_LRCK(B):Audio Link Word Select(B);
				TMR3:Timer3 Clock Input;
		19		SFC1_DO(D0):SFC1 Data Out(nor flash);
				PA_EN:PA Enable;
21	PC2	I/O	GPIO	SPI0_DOC(0):SPI0 Data Out(C);
				ALNK_SCLK(B):Audio Link Serial Clock(B);
				TMR1:Timer1 Clock Input;
				SFC1 CLK:SFC1 Clock(nor flash);
				SPI0 CLKC:SPI0 Clock(C);
22	PC1	I/O	GPIO	ALNK DAT1(B):Audio Link Data1(B);
		\sim		TMR5:Timer5 Clock Input;
		2 2		PWMCH1L:Motor PWM Channel1(L);
				SFC1 D3:SFC1 Data3(nor flash);
				SPI0 DAT3C(3):SPI0 Data3(C);
23	PC0	I/O	GPIO	ALNK DAT0(B):Audio Link Data0(B);
				PWMCH1H:Motor PWM Channell(H);
24	PC8	I/O	GPIO	SPI2DIB:SPI2 Data In(B);
L 2+	100	1/0	GHO	` '
			LICD Magating Date	SPI2DOB:SPI2 Data Out(B);
25	USBDM	I/O	USB Negative Data	IICO_SDA_A:IICO SDA(A);
			(pull down)	ADC11:ADC Input Channel 11;
				UART1RXB:Uart1 Data Input(B);



26	USBDP	I/O	USB Positive Data (pull down)	SPI2CLKB:SPI2 Clock(B); IIC0_SCL_A:IIC0 SCL(A); ADC10:ADC Input Channel 10; UART1TXB:Uart1 Data Output(B);
27	PA11	I/O	GPIO	LCD_SPID3(A); FPIN0;
28	PA10	I/O	GPIO	LCD_SPID2(A); FPIN3;
29	PA9	I/O	GPIO	LCD_SPID1(DI)(A); PWMCH0H:Motor PWM Channel0(H);
30	PA8	I/O	GPIO	LCD_SPID0/DO(A); PLNK_DAT1/ANCDE; ALNK_LRCK(A):Audio Link Word Select(A); ADC3:ADC Input Channel 3; UART2RXB:Uart2 Data Input(B);
31	PA7	I/O	GPIO	LCD_SPICLK(A); ALNK_SCLK(A):Audio Link Serial Clock(A); UART2TXB:Uart2 Data Output(B); TMR0:Timer0 Clock Input;
32	PA6	I/O	GPIO	PLNK_DAT0/ANCDR; SPI2DOA:SPI2 Data Out(A); ALNK_DAT3(A):Audio Link Data3(A); ADC2:ADC Input Channel 2; UART0RXA:Uart0 Data Input(A); CAP0:Timer0 Capture;
33	PA5	I/O	GPIO	PLNK_SCLK/ANCCK; SPI2CLKA:SPI2 Clock(A); ALNK_DAT2(A):Audio Link Data2(A); ADC1:ADC Input Channel 1; UART0TXA:Uart0 Data Output(A); PWM5:Timer5 PWM Output;
34	PA4	I/O	GPIO	MIC_BIAS1:MIC1 Bias Output(Built-in resistor); MIC1_N:Different MIC1 Negative; AMUX_B1:Analog Channel B1 input; SPI2DIA:SPI2 Data In(A); ALNK_DAT1(A):Audio Link Data1(A); CAP2:Timer2 Capture;
35	PA3	I/O	GPIO	MICIN1:MIC1 Input Channel 1; MIC1_P:Different MIC1 Positive; AMUX_B0:Analog Channel B0 input; SPI1DOA:SPI1 Data Out(A); ALNK_DAT0(A):Audio Link Data0(A); PWM1:Timer1 PWM Output;



				MIC_BIAS0:MIC0 Bias Output(Built-in resistor);			
				MIC0_N:Different MIC0 Negative;			
				AMUX_A1:Analog Channel A1 input;			
36	PA2	I/O	GPIO	CLKOUT1:Clock Out1;			
30	1 AZ	1/0	GHO	SPI1CLKA:SPI1 Clock(A);			
				ALNK_MCLKA:ALNK Master Clock(A);			
				UART1RXA:Uart1 Data Input(A);			
				CAP3:Timer3 Capture;			
				MICIN0:MIC0 Input Channel 0;			
				MIC0_P:Different MIC0 Positive;			
37	PA1	I/O	GPIO	AMUX_A0:Analog Channel A0 input;			
3/	PAI	1/0	GPIO	SPI1DIA:SPI1 Data In(A);			
				UART1TXA:Uart1 Data Output(A);			
				PWM0:Timer0 PWM Output;			
20	DAO	1/0	CNIC	MICLDO:Microphone linear voltage regulator output;			
38	PA0	I/O	GPIO	ADC0:ADC Input Channel 0;			
39	AVSS	G	A	Audio analog ground;			
40	VCM	P	45	Audio analog reference bias;			
41	DACRP	AO		Right channel audio output positive;			
42	DACLP	AO		Left channel audio output positive;			
42	PE6	I/O	GPIO	SDPG:SD card power gate;			
43	PE5	I/O	GPIO	//٧			
				MICIN2:MIC2 Input Channel 2;			
44	PG8	I/O	GPIO	MIC2_P:Different MIC2 Positive;			
				AMUX_C0:Analog Channel C0 input;			
	A	1		LCD_SPID3(B);			
				MIC_BIAS2:MIC2 Bias Output(Built-in resistor);			
45	PG7	I/O	GPIO	MIC2_N:Different MIC2 Negative;			
		(A		AMUX_C1:Analog Channel C1 input;			
				ADC15:ADC Input Channel 15;			
				LCD_SPID2(B);			
				MICIN3:MIC3 Input Channel 3;			
46	PG6	I/O	GPIO	MIC3_P:Different MIC3 Positive;			
				AMUX_D0:Analog Channel D0 input;			
				FPIN2;			
				LCD_SPID1/DI(B);			
				MIC_BIAS3:MIC3 Bias Output(Built-in resistor);			
	nc.	1/0	GN/O	MIC3_N:Different MIC3 Negative;			
47	PG5	I/O	GPIO	AMUX_D1:Analog Channel D1 input;			
				ADC14:ADC Input Channel 14;			
				TMR3CK;			
40	DC4	1/0	GPIO	LCD_SPID0/DO(B);			
48	PG4	I/O	(pull up)	PWMCH3L:Motor PWM Channel3(L);			



				LCD_SPICLK(B);
49	PG3	I/O	GPIO	TDM_MCLK;
				PWMCH3H:Motor PWM Channel3(H);
				TDM_DAT;
50	PG2	I/O	GPIO	SD0_CLKB:SD0 Clock(B);
				PWMCH2L:Motor PWM Channel2(L);
51	PG1	I/O	GPIO	TDM_SYN; SD0_CMDB:SD0 CMD(B); ADC13:ADC Input Channel 13; PWMCH2H:Motor PWM Channel2(H);
52	PG0	I/O	GPIO	TDM_CLK; LVD:Low Voltage Detect; SD0_DATB:SD0 Data(B); ADC12:ADC Input Channel 12; TMR2CK;
BOM	VSS	G		System ground;

Pin Type	Description	Pin Type	Description
P	Power	I/O	Input or Output
PO	Power Output	I	Input
PI	Power Input	0	Output
G	Ground	RFI	Radio frequency interface
AO	Analog Output		



3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-40	+85	°C
Tstg	Storage temperature	-65	+150	°C
VBAT	Supply Voltage	-0.3	4.5	V
VPWR	Charger Voltage	-0.3	6	V
V _{IOVDD}	Voltage applied at IOVDD	-0.3	3.6	V
V_{GPIO}	Voltage applied to GPIO	-0.3	IOVDD+0.3	V
V _{HVIO}	Voltage applied to High Voltage Resistant IO	-0.3	+5.5	V

Note: The chip can be damaged by any stress in excess of the absolute maximum ratings listed below

3.2 PMU Characteristics

Table 3-2

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
VBAT	Voltage Input	2.2	3.7	4.5	V	163
VPWR	Charger supply Voltage	4.5	5.0	5.5	V	
Operating mode				/ /	$\langle \nabla$	
IOVDD	Voltage output	2.0	3.0	3.4	V	VBAT = 4.2V, 10mA loading
10 V D D	Loading current		/_ <	120	mA	IOVDD=3V@VBAT = 4.2V
	Voltage output	1.0	1.25	1.4	V	IOVDD=3.0V, 10mA loading
	7 1		-	100	mA	DCVDD=1.25V@IOVDD=3.0v
DCVDD		-				On LDO mode
	Loading current					DCVDD=1.25V@IOVDD=3.0v
			_	160	mA	On DC-DC mode
$V_{ m LVD}$	Voltage input	1.8	2.5	2.5	V	Low-Voltage Detection for IOVDD
Low Power mode						
IOVDD	Loading current	_	_	10	mA	IOVDD=3V@VBAT = 4.2V



3.3 Battery Charge

Table 3-3

Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
V_{PWR}	Charge Input Voltage Range	4.5	5	5.5	V	_
V _{BAT Float}	Battery Charge Termination Voltage	4.15	4.2	4.25	V	VPWR>4.5V
V BAT Float	Battery Charge Termination Voltage	4.30	4.35	4.40	V	VPWR>4.65V
I_{BAT}	Fast Charge Current	15	_	200	mA	VBAT=4.0V@VPWR=5.0V
I _{END}	Charge Termination Current Threshold	2	-	30	mA	-
V_{Trikl}	Trickle Charge Voltage	-	3.0	-3	V	VPWR>4.5V
I_{Trikl}	Trickle Charge Current	1.5	-	30	mA	$V_{\mathrm{BAT}}\!\!<\!\!V_{\mathrm{Trikl}}$

3.4 IO Input/Output Electrical Logical Characteristics

Table 3-4

GPIO input charac	GPIO input characteristics									
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
$ m V_{IL}$	Low-Level Input Voltage	-0.3	/- , \	0.3* IOVDD	V	IOVDD = 3.0V				
$ m V_{IH}$	High-Level Input Voltage	0.7* IOVDD		IOVDD+0.3	V	IOVDD = 3.0V				
High Voltage Resis	High Voltage Resistant IO input characteristics									
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
VIL	Low-Level Input Voltage	-0.3	-	0.3* IOVDD	V	IOVDD = 3.0V				
$ m V_{IH}$	High-Level Input Voltage	0.7* IOVDD	_	+5V	V	IOVDD = 3.0V				
GPIO & High Volt	age Resistant IO outp	ut characteristic	s							
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions				
$ m V_{OL}$	Low-Level Output Voltage	_	_	0.1* IOVDD	V	IOVDD = 3.0V				
$ m V_{OH}$	High-Level Output Voltage	0.9* IOVDD	_	_	V	IOVDD = 3.0V				



3.5 Internal Resistor Characteristics

Table 3-5

Port	Drive Current		Internal Pull-Up Resistor	Internal Pull-Down Resistor	Comment
PA0~PA11	HD1,HD0==0,0	2.4mA			
PC0~PC5,PC8	HD1,HD0==0,1	8mA	10K	10K	
PG0~PG8	HD1,HD0==1,0	26mA	101	101	
PE5,PE6	HD1,HD0==1,1	46mA			1. PB1, PG4 default pull up
PB1~PB9 PC6 PP0(VPWR)	8mA (High Voltage Resistant) 4mA 4mA		10K	10K	USBDM & USBDP default pull down Internal pull-up/pull-down resistance accuracy ±20%
USBDP			1.5K	15K	
USBDM			180K	15K	

3.6 Audio DAC Characteristics

Table 3-6

Parameter	MODE	Min	Тур	Max	Unit	Test Conditions
Frequency Response	4	20	W-10	20K	Hz	
Output Series	Differential		1		Vrms	
Output Swing	Single-ended		520	(=)	mVrms	1KHz/0dB
THD+N	Differential		-70		dB	10k ohm loading
I IID+N	Single-ended		-70	_	dB	With A-Weighted Filter
S/N	Differential		104	_	dB	
5/19	Single-ended	/<	98	_	dB	
	Differential	1//	104	_	dB	1KHz/-60dB
Dynamic Range	Cinala andad		98		dB	10k ohm loading
	Single-ended	_	96	_	ав	With A-Weighted Filter
Noise Floor	Differential	_	5.8	_	uVrms	A-Weighted Filter
NOISE PIOUI	Single-ended	_	5.8	_	uVrms	A-weighted Filter

3.7 Audio ADC Characteristics

Table 3-7

Parameter	Min	Тур	Max	Unit	Test Conditions	
D		0.4		4D	Fsample=44.1kHz,Gain=0dB	
Dynamic Range	_	94	_	dB	Fin=1KHz 590mVrms	
S/N	_	95	_	dB	Fsample=44.1kHz,Gain=0dB	
THD+N	_	-75	_	dB	Fin=1KHz 590mVrms	
S/N	_	76	_	dB	Fsample=44.1kHz,Gain=18dB	
THD+N	_	-73	_	dB	Fin=1KHz 75mVrms	



3.8 BT Characteristics

3.8.1 Transmitter BDR & EDR

Basic Data Rate

Table 3-8

Busic Butu Itute						
Parameter		Min	Тур	Max	Unit	Test Conditions
RF Transmit Power			7.0		dBm	
RF Power Control Rar	ige		18.2		dB	25°C,
20dB Bandwidth			950		KHz	Power Supply
	+2MHz		-28		dBm	
Adjacent Channel Transmit	-2MHz		-34	3	dBm	VBAT=3.7V
Power	+3MHz		-30		dBm	2441MHz
	-3MHz		-43		dBm	

Enhanced Data Rate		Table 3-	9	X		6
Parameter		Min	Тур	Max	Unit	Test Conditions
Relative Power	A		-2.5		dB	
π/4 DQPSK Modulation	DEVM RMS		6		%	
·	DEVM 99%		11		%	25℃
Accuracy	DEVM Peak		16		%	Power Supply
	+2MHz		-28		dBm	VBAT=3.7V
Adjacent Channel Transmit	-2MHz		-34		dBm	2441MHz
Power	+3MHz		-30		dBm	
	-3MHz	100	-43		dBm	



3.8.2 Receiver BDR & EDR

Basic Data Rate

Table 3-10

Parameter		Min	Тур	Max	Unit	Test Conditions
Sensitivity			-92		dBm	
Co-channel Interference Rejection			10		dB	25°C
	+1MHz		-4		dB	Power Supply
	-1MHz		-3		dB	
Adjacent Channel Interference	+2MHz		-39		dB	VBAT=3.7V
Rejection	-2MHz		-29		dB	2441MHz
	+3MHz		-45		dB	DH5
	-3MHz		-23	X	dB	

Enhanced Data Rate

Table 3-11

Parameter	Min	Тур	Max	Unit	Test Conditions	
Sensitivity		-95	-94		dBm	
Co-channel Interference Ro		10	1	dB	25°C	
	+1MHz		-4		dB	Power Supply
	-1MHz		-3	0	dB	VBAT=3.7V
Adjacent Channel Interference	+2MHz		-39		dB	VBA1-3./V
Rejection	-2MHz	/.\	-29		dB	2441MHz
	+3MHz		-45		dB	2DH5
	-3MHz	2	-23		dB	



3.8.3 BLE

1M Data Rate

Table 3-12

THI Duta Rute		1401				
Paramete	er	Min	Тур	Max	Unit	Test Conditions
Sensitivit	у		-97		dBm	
RF Transmit I	Power		6.5		dB	
In-band Spurious	M-N =2MHz			-40	dB	
Emission	M-N ≥3MHz			-50	dB	25℃
	Δfl avg		250			Power Supply
Modulation Characteristics	Δf2 99%		200	4		VBAT=3.7V
Characteristics	Δflavg/Δf2avg		0.9		31	2441MHz
Carrier Frequenc	cy Offset	-10	4	+10	KHz	
Frequency I	Drift	-10		+10	KHz	L
Frequency Dri	ft Rate	-5		+5	KHz/50us	C,

2M Data Rate

Table 3-13

Paramete	r	Min	Тур	Max	Unit	Test Conditions
Sensitivity	y		-94		dBm	
RF Transmit P	ower		6.5	60.	dB	
	M-N =4MHz			-40	dB	
In-band Spurious Emission	M-N =5MHz			-40		25°C
	M-N ≥6MHz			-50	dB	Power Supply
	Δf1 avg		500			
Modulation Characteristics	Δf2 99%	A	415			VBAT=3.7V
Characteristics	Δflavg/Δf2avg	-	0.9			2441MHz
Carrier Frequenc	y Offset	-10		+10	KHz	
Frequency D	rift	-10		+10	KHz	
Frequency Drif	t Rate	-5		+5	KHz/50us	

Long Range

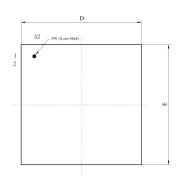
Table 3-14

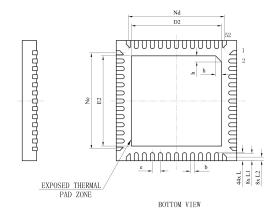
Parameter	Min	Тур	Max	Unit	Test Conditions
Sensitivity LE 125K(S8)		-104		dBm	VBAT=3.7V,25°C
Sensitivity LE 500K(S2)		-101		dBm	2441MHz



4 Package Information

4.1 QFN52_6×6mm





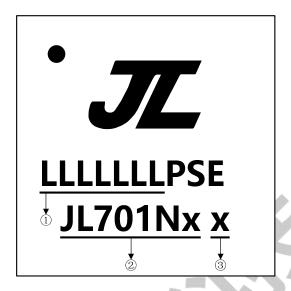
SYMBOL	MILLIMETER					
SYMBOL	MIN	NOM	MAX			
Λ	0.70	0. 75	0.80			
A1	_	0.035	0.05			
b	0. 15	0. 20	0. 25			
c	0.18	0. 20	0. 25			
D	5. 90	6.00	6. 10			
D2	4. 40	4. 50	4.60			
е	0. 40BSC					
Nd	4	. 80BSC				
Е	5. 90	6.00	6. 10			
E2	4. 40	4. 50	4. 60			
Ne	4	. 80BSC				
L	0.35	0.40	0.45			
L1	0.31	0.36	0. 41			
L2	0.13	0.18	0. 23			
h	0. 25	0.30	0. 35			
L/F载体尺寸 (mil)		185*185	5			



Figure 4-1 JL7012F Package



5 IC Marking Information



- ① LLLLLLL: Production Batch
- ② JL701Nx: Chip Model
- 3 Built-in flash size
 - 0: No Flash Memory
 - 2: 2Mbit Flash
 - 4: 4Mbit Flash
 - 8: 8Mbit Flash
 - 6: 16Mbit Flash
 - 3: 32Mbit Flash



6 Solder-Reflow Condition

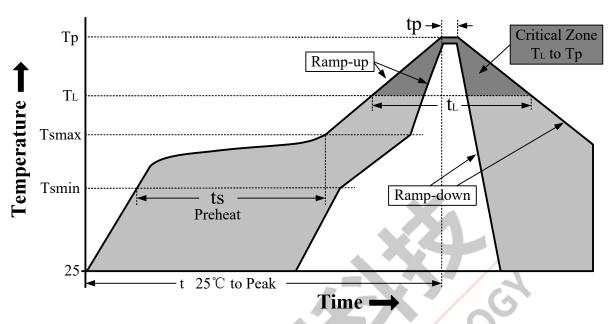


Figure 6-1 Classification Reflow Profile

Classification Profiles

Table 6-1

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
	Temperature Min (T _{smin})	100 °C	150 °C
Preheat/	Temperature Max (T _{smax})	150 °C	200 °C
Soak	Time (ts) from (T _{smin} to T _{sma} x)	60-120 seconds	60-180 seconds
Average ra	amp-up rate $(T_{\text{smax}} \text{ to } T_p)$	3 °C/second max	3 °C/second max
Liquidous temperature (T _L)		183 ℃	217 ℃
Time (t _L) 1	maintained above T _L	60-150 seconds	60-150 seconds
Peak pack	age body temperature (T _p)	See Table 6-2.	See Table 6-3.
Time within 5°C of actual Peak Temperature (tp)		10-30 seconds	20-40 seconds
Ramp-dov	vn rate (T _p to T _L)	6 °C/second max.	6 °C/second max.
Time 25 °C	C to peak temperature	6 minutes max.	8 minutes max.

Note 1: All temperatures refer to topside of the package, measured on the package body surface.

Note 2: Time within 5°C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" minimum and "user" maximum.

SnPb - Classification Temperature

Table 6-2

Package	Volume mm ³	Volume mm ³
Thickness	< 350	≥ 350
<2.5 mm	240 +0/-5 °C	225 +0/-5 °C
≥ 2.5 mm	225 +0/-5 °C	225 +0/-5 °C



Pb-free - Classification Temperature Table 6-3

Package	Volume mm ³	Volume mm ³	Volume mm ³
Thickness	< 350	350 - 2000	> 2000
< 1.6mm	260 °C	260 °C	260 °C
1.6 mm - 2.5mm	260 °C	250 °C	245 ℃
> 2.5mm	250 °C	245 °C	245 °C





7 Revision History

Date	Revision	Description
2022.02.09	V1.0	Initial Release;
2022.04.08	V1.1	Modify Pin Assignment (PIN41 update to DACRP); Update DAC Characteristics.
2022.06.08	V1.2	Add IC Marking Information & Solder-Reflow Condition; Add BLE Parameters.

